






Substitute for form 1449B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	12/800,998
				Filing Date	March 16, 2004
				First Named Inventor	Lu
				Group Art Unit	~813
				Examiner Name	SAK CHEN
Sheet	1	of	2	Attorney Docket Number	95153-DIV

OTHER PRIOR ART — NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		J. STOEMENOS et al, "Dislocation formations related with high oxygen dose implantation on silicon." J. App1 Phys., 69(1991), p.793.	
		D. HILL et al, "The reduction of dislocations in oxygen implanted silicon on insulator layers by sequential implantation and annealing." J. App1 Phys., 63(1998), p. 4933.	
		S. NAKASHIMA et al, "Investigations on high temperatures thermal oxidataion press at top and bottom interfaces of top silicon of SIMOX wafers." J. Electrochem. Soc., p. 244	
		L. NESBIT et al, "Microstructure of silicon implanted with high dose of nitrogen and oxygen." J. Electrochem. Soc., 133(1986), p.1186.	

Examiner Signature		Date Considered	1/4/05
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Unique citation designation number. <sup>2</sup> Applicant is to place a check mark here is English language Translation is attached.

Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	10/800,998
				Filing Date	March 16, 2004
				First Named Inventor	LU
				Group Art Unit	2813
				Examiner Name	JACK CHEN
Sheet	2	of	2	Attorney Docket Number	95153-DIV

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee of Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code* (if known)			
		4,786,608		Griffith	11/1998	
		5,888,297		Ogura	3/1999	

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				

Examiner Signature		Date Considered	1/4/05
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<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3) <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.